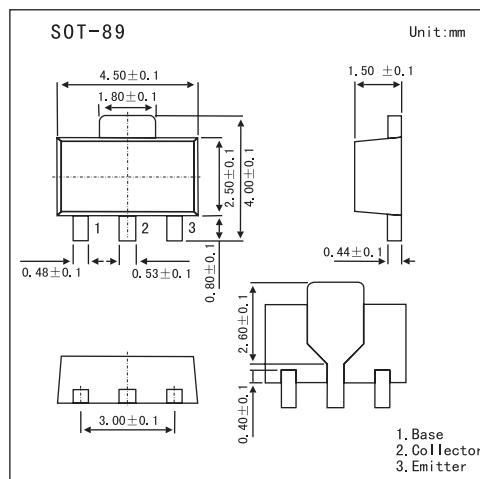


■ Features

- Low Saturation Voltage: $V_{CE(sat)} = 0.5V$ (max) ($I_c = 500mA$)
- High Speed Switching Time: $t_{stg} = 0.4\mu s$ (typ.)
- Small Flat Package
- $P_c = 1$ to $2W$ (mounted on ceramic substrate)
- Complementary to 2SA1735



■ Absolute Maximum Ratings $T_a = 25^\circ C$

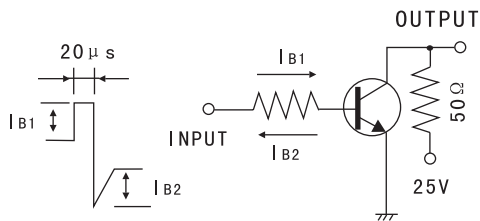
Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_c	1	A
Base Current	I_B	0.2	A
Collector Power Dissipation	P_c	500	mW
	P_{c^*}	1000	
Junction temperature	T_j	150	$^\circ C$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ C$

* Mounted on ceramic substrate ($250\text{ mm}^2 \times 0.8\text{ t}$)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = 80V, I_E = 0$			0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6V, I_C = 0$			0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	50			V
DC Current Gain	h_{FE}	$V_{CE} = 2V, I_C = 100mA$	120		400	
		$V_{CE} = 2V, I_C = 700mA$	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 25mA$			0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 25mA$			1.2	V
Transition Frequency	f_T	$V_{CE} = 2V, I_C = 100mA$		100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		10		pF
Turn-On Time	t_{on}	See Test Circuit.		0.1		μs
Storage Time	t_{stg}			0.4		
Fall Time	t_f			0.1		

■ Test Circuit

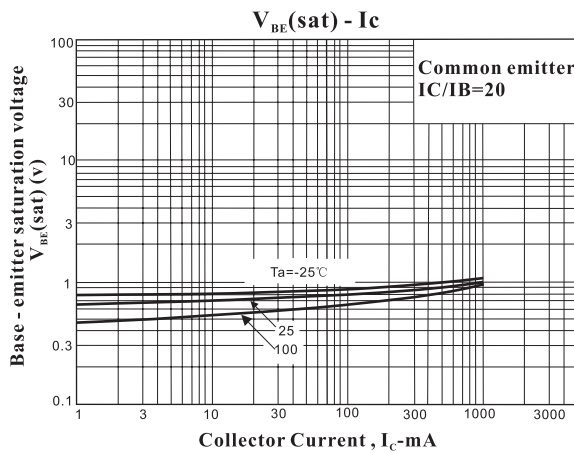
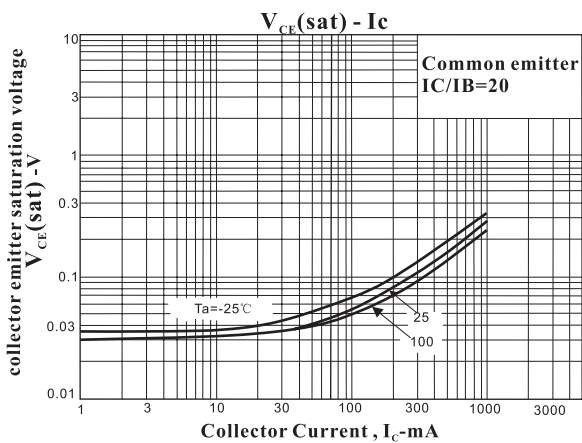
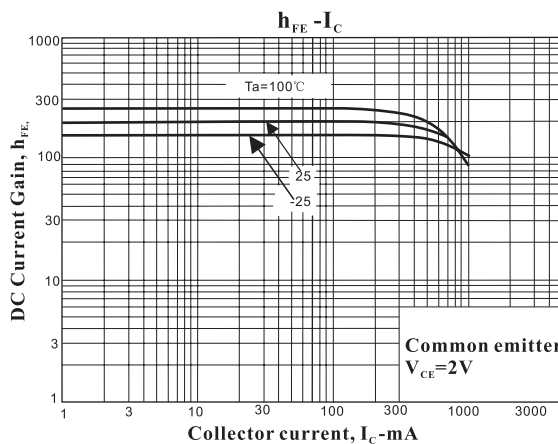
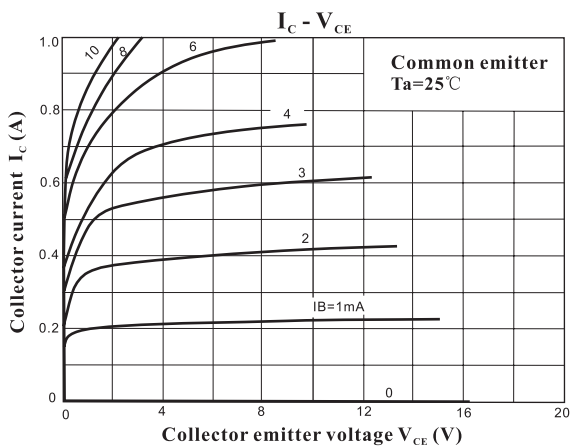


$I_{B1} = -I_{B2} = 35\text{mA}$, DUTY CYCLE $\leq 1\%$

■ Marking

Marking	KC
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■ Electrical Characteristics Curves





2SC4540

